



# FFH30S60S Stealth 2 Rectifier

### **Features**

- High Speed Switching,  $t_{rr}$  < 40ns @  $I_F$  = 30A
- High Reverse Voltage and High Reliability
- · RoHS compliant

### **Applications**

- · General Purpose
- · Switching Mode Power Supply
- Boost Diode in continuous mode power factor corrections
- · Power switching circuits

# 30A, 600V Stealth 2 Rectifier

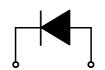
The FFH30S60S is stealth2 rectifier with soft recovery characteristics. It is silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as freewheeling of boost diode in switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.



### **Pin Assigments**





1. Cathode 2. Anode

## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{RRM}$	Peak Repetitive Reverse Voltage	600	V
$V_{RWM}$	Working Peak Reverse Voltage	600	V
$V_R$	DC Blocking Voltage	600	V
I <sub>F(AV)</sub>	Average Rectified Forward Current @ T <sub>C</sub> = 102°C	30	Α
I <sub>FSM</sub>	Non-repetitive Peak Surge Current 60Hz Single Half-Sine Wave	300	А
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-65 to +150	°C

### **Thermal Characteristics**

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Maximum Thermal Resistance, Junction to Case	1.1	°C/W

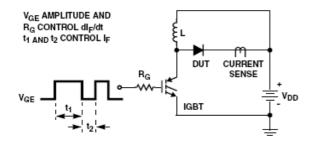
## **Package Marking and Ordering Information**

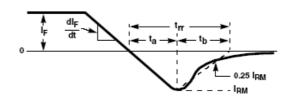
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
F30S60S	FFH30S60STU	TO-247-2L	-	-	50

# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Min.	Тур.	Max.	Units
V <sub>FM</sub> 1	$I_F = 30A$ $I_F = 30A$	$T_{\rm C} = 25^{\rm o}{\rm C}$ $T_{\rm C} = 125^{\rm o}{\rm C}$		2.1 1.6	2.6	V
I <sub>RM</sub> 1	V <sub>R</sub> = 600V V <sub>R</sub> = 600V	$T_{\rm C} = 25^{\rm o}{\rm C}$ $T_{\rm C} = 125^{\rm o}{\rm C}$			100 500	μА
t <sub>rr</sub>	$I_F = 1A$ , di/dt = 100A/ $\mu$ s, $V_R = 30V$	$T_C = 25^{\circ}C$	-	25	35	ns
t <sub>rr</sub> I <sub>rr</sub> S factor Q <sub>rr</sub>	$I_F = 30A$ , di/dt = 200A/ $\mu$ s, $V_R = 390V$	T <sub>C</sub> = 25°C	- - - -	28 2.4 0.9 34	40 - - -	ns A nC
t <sub>rr</sub> I <sub>rr</sub> S factor Q <sub>rr</sub>	$I_F = 30A$ , di/dt = 200A/ $\mu$ s, $V_R = 390V$	T <sub>C</sub> = 125°C	- - -	75 6.3 0.9 236	- - -	ns A nC
W <sub>AVL</sub>	Avalanche Energy ( L = 40mH)		20	=	-	mJ

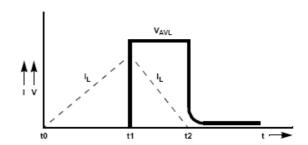
# **Test Circuit and Waveforms**





L = 40mH R < 0.1Ω V<sub>DD</sub> = 50V

 $\begin{aligned} &\mathsf{EAVL} = 1/2\mathsf{L}12 \; [\mathsf{V}_{\mathsf{R}(\mathsf{AVL})}/(\mathsf{V}_{\mathsf{R}(\mathsf{AVL})} \cdot \mathsf{V}_{\mathsf{DD}})] \\ &\mathsf{Q1} = \mathsf{IGBT} \; (\mathsf{BV}_{\mathsf{CES}} > \mathsf{DUT} \; \mathsf{V}_{\mathsf{R}(\mathsf{AVL})}) \end{aligned}$ CURRENT SENSE  $V_{DD}$  $\nu_{DD}$ 



Notes: 1: Pulse: Test Pulse width =  $300\mu$ s, Duty Cycle = 2%

# **Typical Performance Characteristics**

Figure 1. Typical Forward Voltage Drop vs. Forward Current

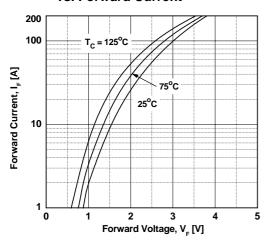


Figure 3. Typical Junction Capacitance

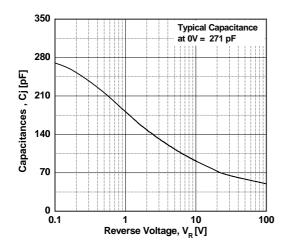


Figure 5. Typical Reverse Recovery Current vs. di/dt

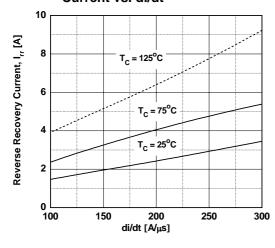


Figure 2. Typical Reverse Current vs. Reverse Voltage

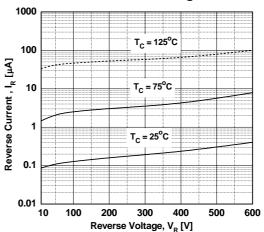
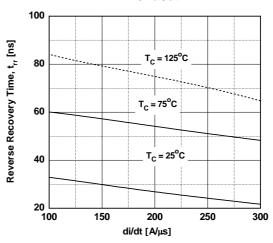
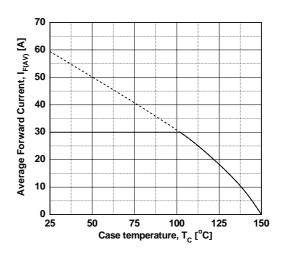


Figure 4. Typical Reverse Recovery Time vs. di/dt

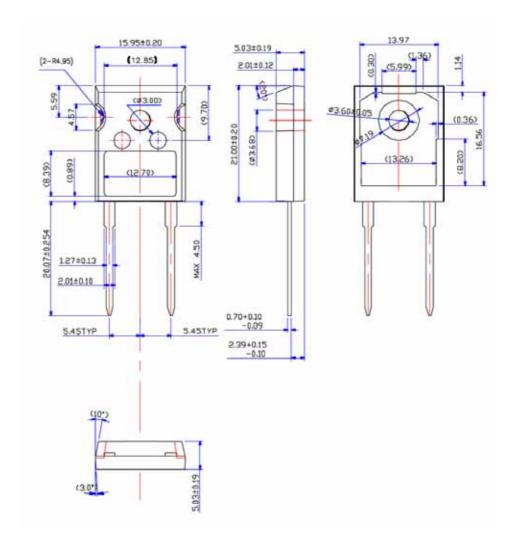


**Figure 6. Forward Current Derating Curve** 



## **Mechanical Dimensions**

# TO-247-2L



Dimensions in Millimeters



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